NOT RECOMMENDED FOR NEW DESIGN
CONTACT US

Green

DMJ70H600HCT

700V N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV_{DSS}	$R_{DS(ON)}$ Max	I_D Max T_C = +25°C
700V	0.6Ω @ V_{GS} = 10V	8.5A

Features

- Low $R_{DS(ON)}$ – Minimizes On-State Losses
- Low Input Capacitance
- Fast Switching Speed
- **Lead-Free Finish; RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free "Green" Device (Note 3)**
- **For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/104/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative.**
  https://www.diodes.com/quality/product-definitions/

Description and Applications

This MOSFET is designed to minimize the on-state resistance ($R_{DS(ON)}$) yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

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- Motor controls
- DC-DC converters
- Power managements

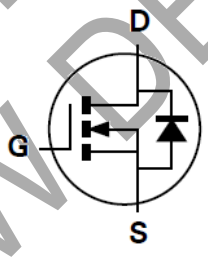
Mechanical Data

- Package: TO220AB
- Package Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Terminal Connections: See Diagram
- Terminals: Finish – Matte Tin Annealed over Copper Leadframe Solderable per MIL-STD-202, Method 208 e3
- Weight: 2.24 grams (Approximate)

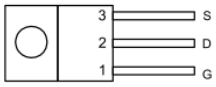
TO220AB (Type TH)

Top View

Bottom View



Equivalent Circuit



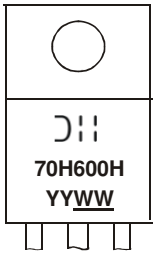
Top View
Pin Out Configuration

Ordering Information (Note 4)

Part Number	Package	Packing	
		Qty.	Carrier
DMJ70H600HCT	TO220AB (Type TH)	50 Pieces	Tube

Notes:
1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



= Manufacturer's Marking
70H600H = Product Type Marking Code
YYWW = Date Code Marking
YY = Last Two Digits of Year (ex: 22 = 2022)
WW = Week Code (01 to 53)

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Drain-Source Voltage		V_{DSS}	700	V
Gate-Source Voltage		V_{GSS}	±30	V
Continuous Drain Current (Note 5) V_{GS} = 10V	T_C = +25°C T_C = +100°C	I_D	8.5 5.3	A
Maximum Body Diode Forward Current (Note 5)		I_S	8.5	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)		I_{DM}	34	A
Pulsed Body Diode Continuous Current (10µs Pulse, Duty Cycle = 1%)		I_{SM}	34	A
Avalanche Current, L = 60mH		I_{AS}	1.8	A
Avalanche Energy, L = 60mH		E_{AS}	97	mJ

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	T_C = +25°C	P_D	104	W
Thermal Resistance, Junction to Case (Note 5)		$R_{\theta JC}$	1.2	°C/W
Total Power Dissipation (Note 6)	T_A = +25°C	P_D	2.3	W
Thermal Resistance, Junction to Ambient (Note 6)		$R_{\theta JA}$	55	°C/W
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV_{DSS}	700	—	—	V	V_{GS} = 0V, I_D = 250µA
Zero Gate Voltage Drain Current	I_{DSS}	—	—	1	µA	V_{DS} = 700V, V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	—	—	100	nA	V_{GS} = ±30V, V_{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	$V_{GS(TH)}$	2	3.7	5	V	V_{DS} = V_{GS}, I_D = 250µA
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	0.47	0.6	Ω	V_{GS} = 10V, I_D = 2.4A
Diode Forward Voltage	V_{SD}	—	0.8	1.3	V	V_{GS} = 0V, I_S = 4.6A
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C_{iss}	—	570	—	pF	V_{DS} = 25V, f = 1MHz, V_{GS} = 0V
Output Capacitance	C_{oss}	—	628	—		
Reverse Transfer Capacitance	C_{rss}	—	40	—		
Gate Resistance	R_g	—	2.5	—	Ω	V_{DS} = 0V, V_{GS} = 0V, f = 1MHz
Total Gate Charge	Q_g	—	17.4	—	nC	V_{DD} = 380V, I_D = 4.6A, V_{GS} = 10V
Gate-Source Charge	Q_{gs}	—	3	—		
Gate-Drain Charge	Q_{gd}	—	8.7	—		
Turn-On Delay Time	$t_{D(ON)}$	—	20	—	ns	V_{DD} = 380V, V_{GS} = 10V, R_G = 25Ω, I_D = 4.6A
Turn-On Rise Time	t_R	—	50	—		
Turn-Off Delay Time	$t_{D(OFF)}$	—	76	—		
Turn-Off Fall Time	t_F	—	37	—		
Body Diode Reverse Recovery Time	t_{RR}	—	194	—	ns	I_S = 4A, di/dt = 100A/µs
Body Diode Reverse Recovery Charge	Q_{RR}	—	1.6	—	µC	

Notes: 5. Device mounted on infinite heatsink.
6. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
7. Short duration pulse test used to minimize self-heating effect.
8. Guaranteed by design. Not subject to production testing.

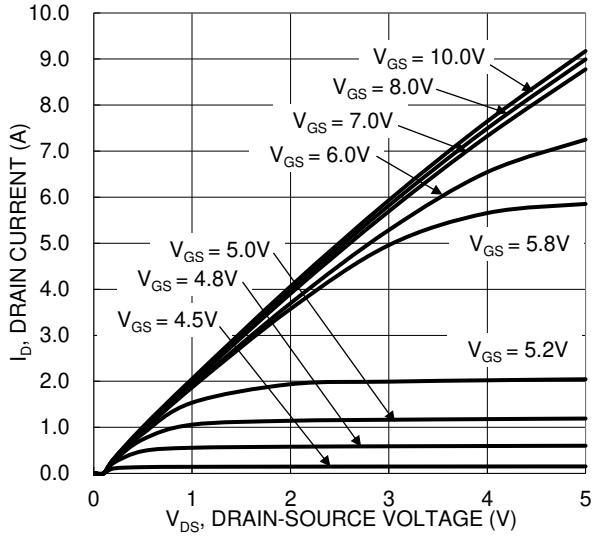


Figure 1. Typical Output Characteristic

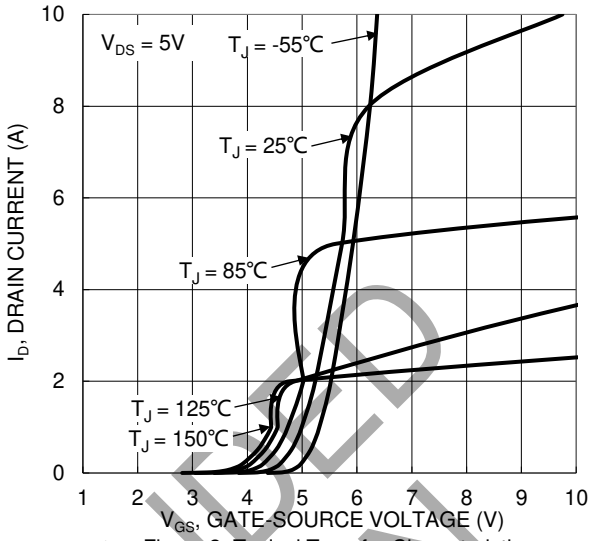


Figure 2. Typical Transfer Characteristic

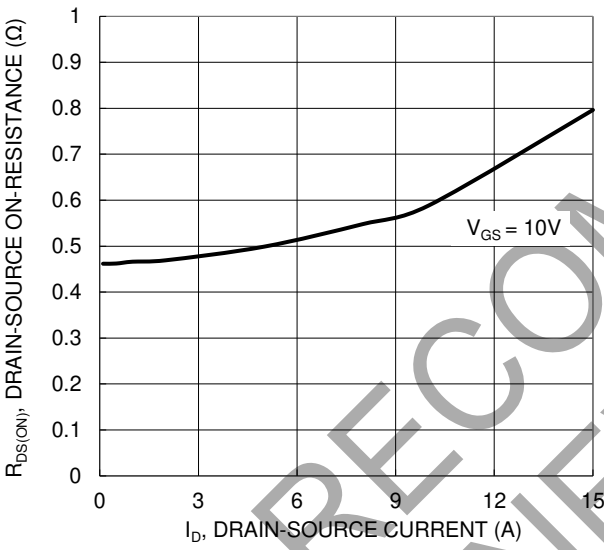


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

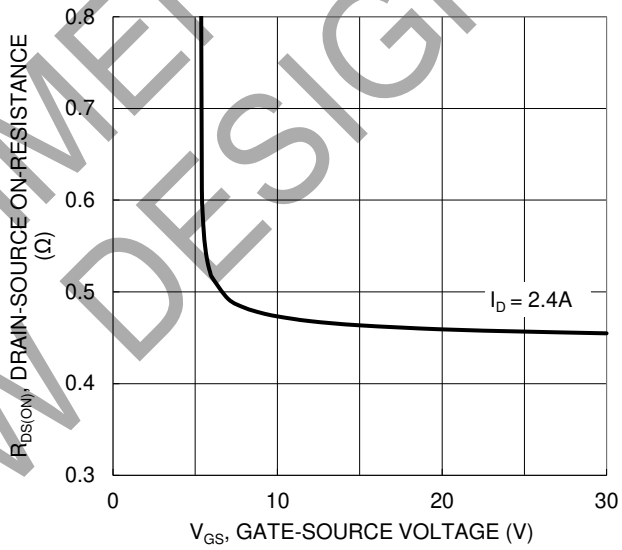


Figure 4. Typical Transfer Characteristic

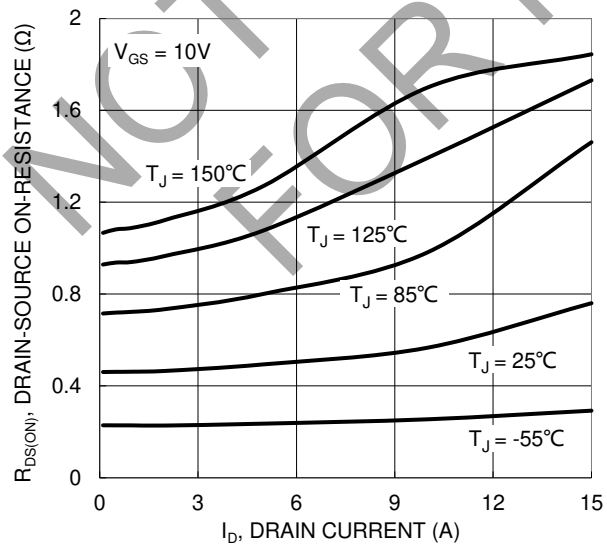


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature

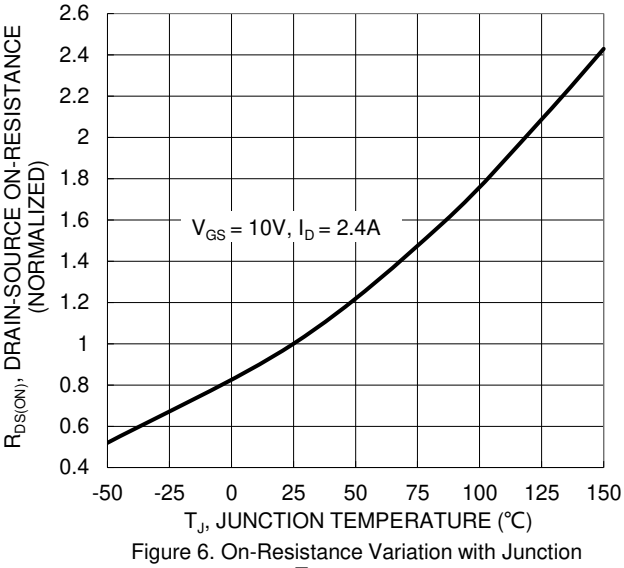


Figure 6. On-Resistance Variation with Junction Temperature

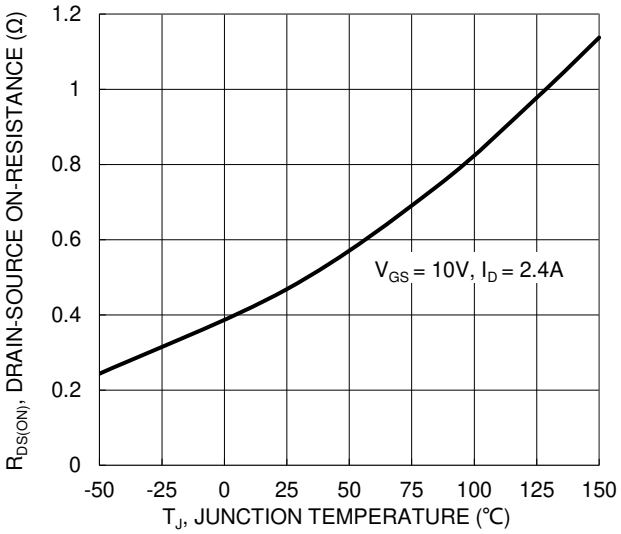


Figure 7. On-Resistance Variation with Junction Temperature

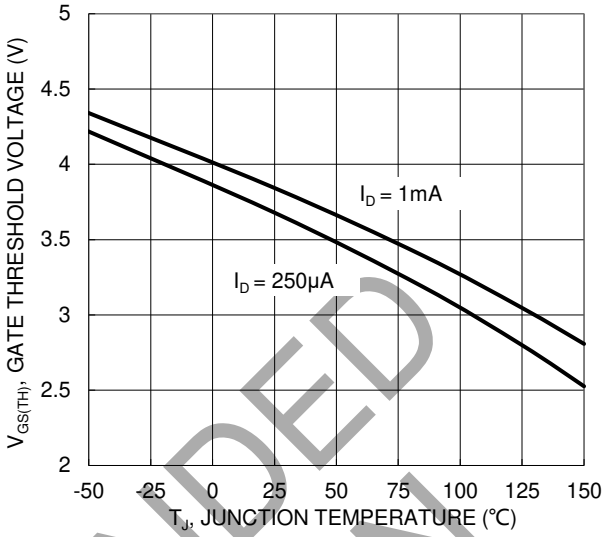


Figure 8. Gate Threshold Variation vs. Junction Temperature

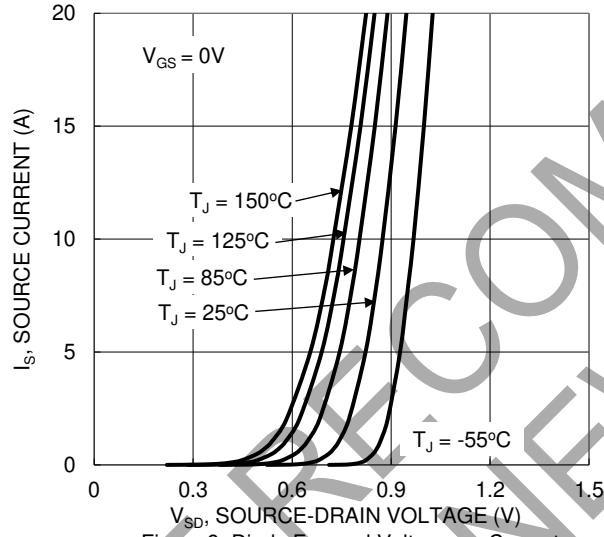


Figure 9. Diode Forward Voltage vs. Current

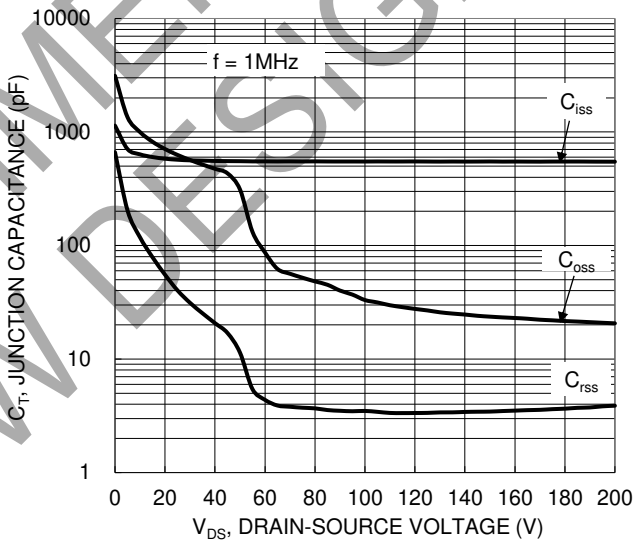


Figure 10. Typical Junction Capacitance

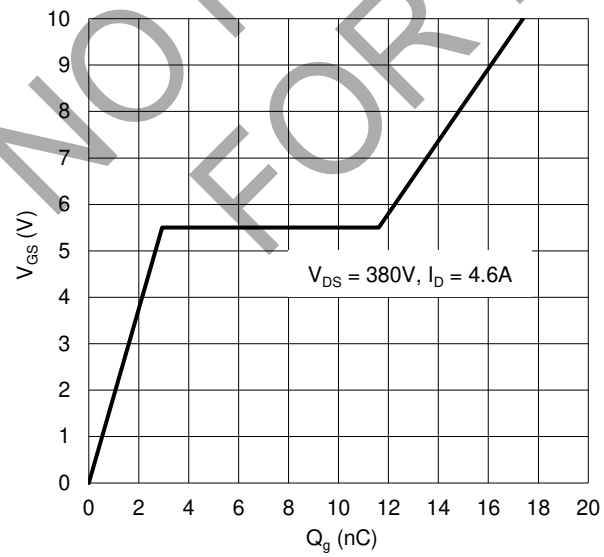


Figure 11. Gate Charge

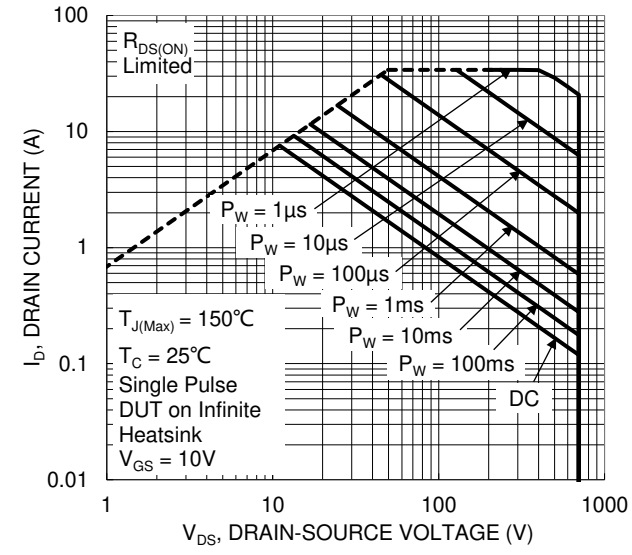


Figure 12. SOA, Safe Operation Area

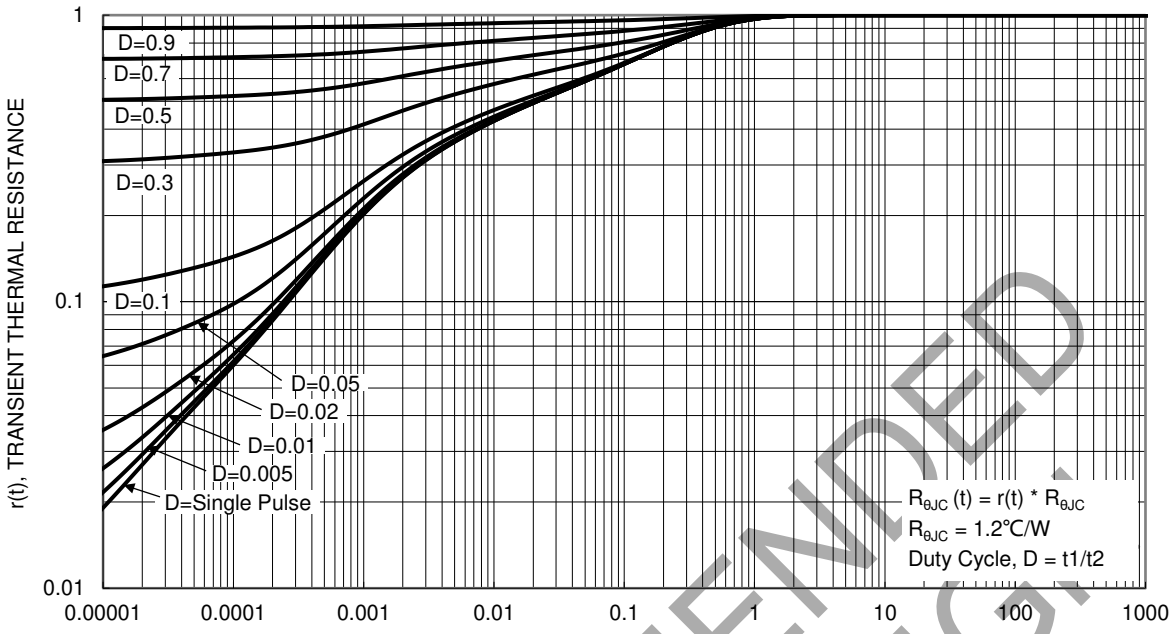
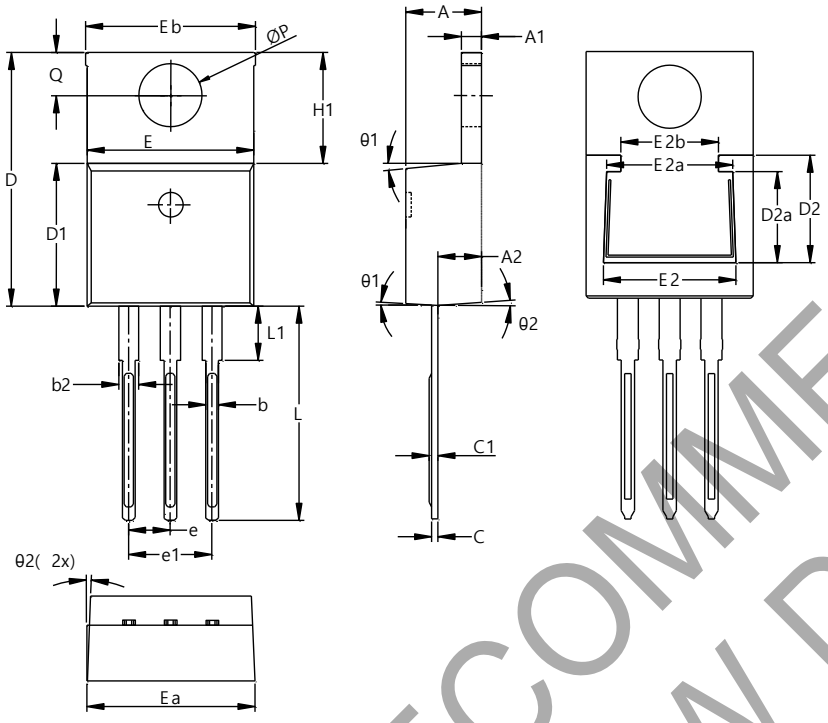


Figure 13. Transient Thermal Resistance

Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

TO220AB (Type TH)



TO220AB (Type TH)			
Dim	**Min**	**Max**	**Typ**
A	4.27	4.87	4.57
A1	1.12	1.42	1.27
A2	2.39	2.99	2.69
b	0.70	1.01	0.81
b2	1.17	1.50	1.27
c	0.30	0.53	0.38
c1	0.38	0.72	0.56
D	14.60	15.40	15.00
D1	8.40	9.00	8.70
D2	5.33	6.63	6.33
D2a	4.54	5.84	5.54
e	2.54 BSC		
e1	5.08 BSC		
E	9.88	10.50	10.16
Ea	9.90	10.45	10.10
Eb	9.90	10.65	10.25
E2	7.06	8.36	8.06
E2a	6.67	7.97	7.67
E2b	4.94	6.24	5.94
H1	5.70	6.65	6.30
L	13.00	13.80	13.40
L1	—	4.10	3.75
Q	2.50	2.99	2.74
ØP	3.70	3.99	3.84
θ1	4°	10°	7°
θ2	0°	6°	3°
All Dimensions in mm			

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